

SPEC SHEET (FOR REFERENCE)		SHEET No. G05033A		Rev. 2	Page. 1 of 1	
TYPE:6PT1803N1T *, 6KT1803N1T *						
CHIP SIZE	1.1 * 1.1mm					
WAFER SIZE	6 inch					
Maximum Ratings (Ta=25°C)						
Characteristics	Symbol	Ratings	Unit			
Drain-Source voltage	VDSS	30	V			
Gate-Source voltage	VGSS	±8	V			
WAFER PROBING SPEC (Ta=25°C)						
TEST NO.	MODE	LIMIT			UNIT	CONDITION
		MIN	Typ	MAX		
1	IGSS			±2	uA	VGS=±8.0V, VDS=0V
2	IDSS			500	nA	VDS=30.0V, VGS=0V
3	BVDSS	33.0			V	ID=250uA, VGS=0V
4	Vth	0.45		1.0	V	ID=250uA, VGS=VDS
5	RDS(on) 1		0.05	0.08	Ω	ID=0.95A, VGS=4.5V
6	RDS(on) 2		0.07	0.11	Ω	ID=0.67A, VGS=2.5V
7	RDS(on) 3		0.12	0.21	Ω	ID=0.67A, VGS=1.8V
8	VSD			0.9	V	IS=1A, VGS=0V
※Built in ZD between Gate and Source						

PHENITEC SEMICONDUCTOR Corp.